

PSMN070-200P

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 04 — 14 December 2010

Product data sheet

1. Product profile

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC converters

Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit | |
|------------------|----------------------------------|---|-----|-----|-----|------|--|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 200 | V | |
| I _D | drain current | T _{mb} = 25 °C | - | - | 35 | Α | |
| P _{tot} | total power dissipation | | - | - | 250 | W | |
| Static ch | aracteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 25 \text{ °C}$ | - | 60 | 70 | mΩ | |
| Dynamic | Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10 \text{ V; } I_D = 35 \text{ A;}$ $V_{DS} = 160 \text{ V; } T_j = 25 \text{ °C}$ | - | 28 | - | nC | |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---------------------------|-----------------------|
| 1 | G | gate | | |
| 2 | D | drain | mb | D |
| 3 | S | source | | $G \longrightarrow A$ |
| mb | D | mounting base; connected to drain | 1 2 3 SOT78 (TO-220AB) | mbb076 S |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|----------|--|---------|
| | Name | Description | Version |
| PSMN070-200P | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|--|---|-----|-----|------|
| V _{DS} | drain-source voltage | T _i ≥ 25 °C; T _i ≤ 175 °C | - | 200 | V |
| V_{DGR} | drain-gate voltage | $T_i \ge 25$ °C; $T_i \le 175$ °C; $R_{GS} = 20$ kΩ | - | 200 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | T _{mb} = 100 °C | - | 25 | Α |
| | | T _{mb} = 25 °C | - | 35 | Α |
| I _{DM} | peak drain current | pulsed; T _{mb} = 25 °C | - | 140 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C | - | 250 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| Source-drai | in diode | | | | |
| Is | source current | T _{mb} = 25 °C | - | 35 | Α |
| I _{SM} | peak source current | pulsed; T _{mb} = 25 °C | - | 140 | Α |
| Avalanche r | ruggedness | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 35 \text{ A;} \\ &V_{sup} \leq 50 \text{ V; unclamped; } t_p = 100 \mu\text{s;} \\ &R_{GS} = 50 \Omega \end{split}$ | - | 462 | mJ |
| I _{AS} | non-repetitive avalanche current | $V_{sup} \le 50 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; unclamped$ | - | 35 | Α |

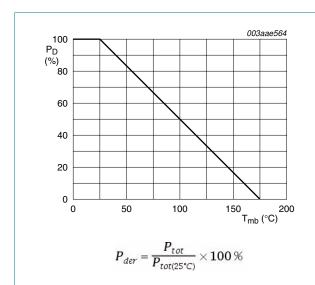


Fig 1. Normalized total power dissipation as a function of mounting base temperature

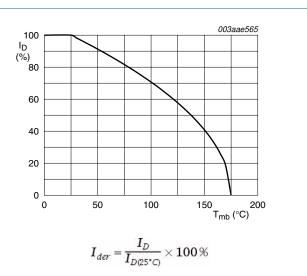


Fig 2. Normalized continuous drain current as a function of mounting base temperature

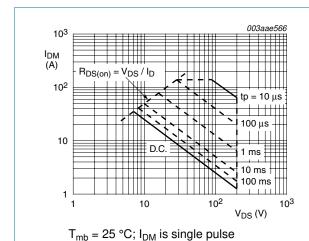


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

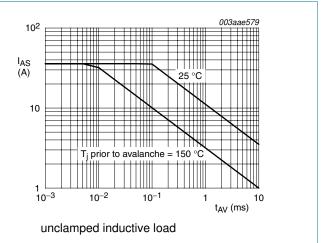


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|-------------|-----|-----|-----|------|
| $R_{th(j\text{-}mb)}$ | thermal resistance from junction to mounting base | | - | - | 0.6 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

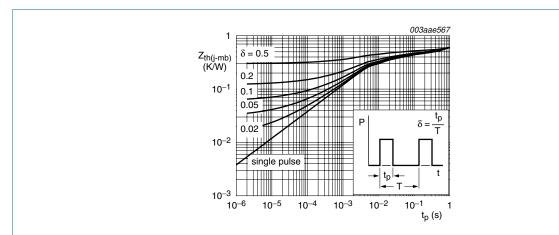
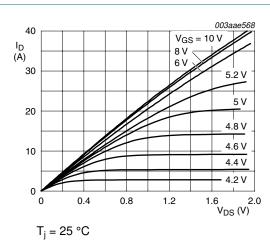


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

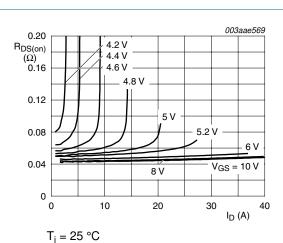
6. Characteristics

Table 6. Characteristics

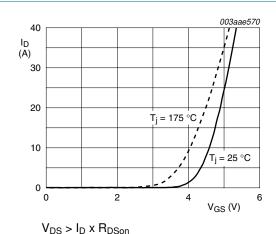
| Table 6. | Characteristics | | | | | |
|---------------------|------------------------------|--|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | 200 | - | - | V |
| | voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 178 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$ | 1 | - | - | V |
| | voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 2 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$ | - | - | 6 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$ | - | - | 500 | μΑ |
| | | $V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.05 | 10 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nA |
| | | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 10 V; I _D = 17 A; T _j = 175 °C | - | - | 203 | mΩ |
| | resistance | $V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 25 \text{ °C}$ | - | 60 | 70 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 35 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 77 | - | nC |
| Q _{GS} | gate-source charge | $T_j = 25 ^{\circ}C$ | - | 16 | - | nC |
| Q_{GD} | gate-drain charge | | - | 28 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$ | - | 4570 | - | рF |
| C _{oss} | output capacitance | | - | 370 | - | рF |
| C_{rss} | reverse transfer capacitance | | - | 160 | - | рF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 100 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$ | - | 22 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$ | - | 100 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 80 | - | ns |
| t _f | fall time | | - | 90 | - | ns |
| L _D | internal drain inductance | measured from tab to centre of die ; $T_j = 25 ^{\circ}\text{C}$ | - | 3.5 | - | nΗ |
| | | measured from drain lead to centre of die ; $T_j = 25 ^{\circ}\text{C}$ | - | 4.5 | - | nΗ |
| Ls | internal source inductance | measured from source lead to source bond pad; $T_j = 25$ °C | - | 7.5 | - | nΗ |
| Source-d | rain diode | | | | | |
| V _{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | - | 160 | - | ns |
| Q _r | recovered charge | $V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$ | - | 1 | - | μC |



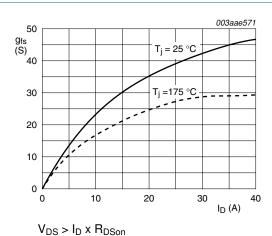
Output characteristics: drain current as a Fig 6. function of drain-source voltage; typical values



Drain-source on-state resistance as a function Fig 7. of drain current; typical values



Transfer characteristics: drain current as a Fig 8. function of gate-source voltage; typical values



Forward transconductance as a function of Fig 9. drain current; typical values

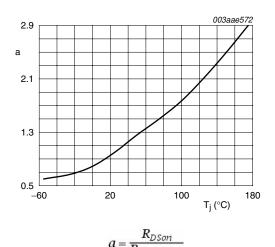


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

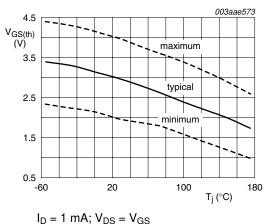


Fig 11. Gate-source threshold voltage as a function of junction temperature

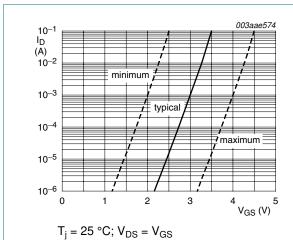
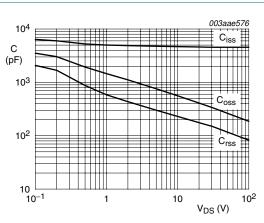


Fig 12. Sub-threshold drain current as a function of gate-source voltage



 $V_{GS} = 0 V$; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

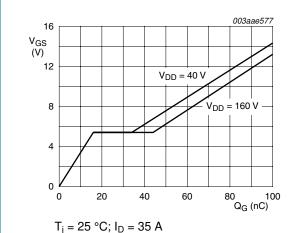
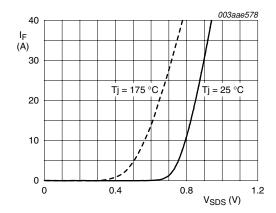


Fig 14. Gate-source voltage as a function of gate

charge; typical values



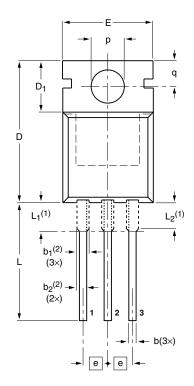
 $V_{GS} = 0 V$

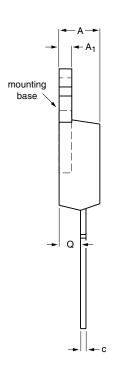
Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

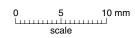
7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

| UNIT | Α | A ₁ | b | b ₁ ⁽²⁾ | b ₂ ⁽²⁾ | С | D | D ₁ | E | е | L | L ₁ ⁽¹⁾ | L ₂ ⁽¹⁾ max. | р | q | Q |
|------|------------|----------------|------------|-------------------------------|-------------------------------|------------|--------------|----------------|-------------|------|--------------|-------------------------------|------------------------------------|------------|------------|------------|
| mm | 4.7 4.1 | 1.40 1.25 | 0.9 0.6 | 1.6 1.0 | 1.3 1.0 | 0.7 0.4 | 16.0 15.2 | 6.6 5.9 | 10.3 9.7 | 2.54 | 15.0 12.8 | 3.30 2.79 | 3.0 | 3.8 3.5 | 3.0 2.7 | 2.6 2.2 |

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|-----------------|----------|------------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | | 08-04-23 08-06-13 |

Fig 16. Package outline SOT78 (TO-220AB)

PSMN070-200P

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|---|--------------|---|-------------------|--|--|
| PSMN070-200P v.4 | 20101214 | Product data sheet | - | PSMN070-200_SERIES_HG v.3 | |
| Modifications: • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. | | | | | |
| | Type num | is have been adapted t liber PSMN070-200P s J-200_SERIES_HG v.3 | eparated from dat | ny name where appropriate. ta sheet | |
| PSMN070-200_SERIES_HG v.3 | 19990801 | Product specification | - | PSMN070-200_SERIES_HG v.2 | |

9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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